

Leo J Schowalter

List of Publications by Year in descending order

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Version: 2024-02-01

18
papers

1,729
citations

516561

16
h-index

839398

18
g-index

18
all docs

18
docs citations

18
times ranked

1361
citing authors

| # | ARTICLE | IF | CITATIONS |
|----|---|-----|-----------|
| 1 | Some effects of oxygen impurities on AlN and GaN. Journal of Crystal Growth, 2002, 246, 287-298. | 0.7 | 350 |
| 2 | The 2020 UV emitter roadmap. Journal Physics D: Applied Physics, 2020, 53, 503001. | 1.3 | 289 |
| 3 | A 271.8 nm deep-ultraviolet laser diode for room temperature operation. Applied Physics Express, 2019, 12, 124003. | 1.1 | 217 |
| 4 | 270 nm Pseudomorphic Ultraviolet Light-Emitting Diodes with Over 60 mW Continuous Wave Output Power. Applied Physics Express, 2013, 6, 032101. | 1.1 | 153 |
| 5 | Ultraviolet semiconductor laser diodes on bulk AlN. Journal of Applied Physics, 2007, 101, 123103. | 1.1 | 144 |
| 6 | High Output Power from 260 nm Pseudomorphic Ultraviolet Light-Emitting Diodes with Improved Thermal Performance. Applied Physics Express, 2011, 4, 082101. | 1.1 | 135 |
| 7 | Large-area AlN substrates for electronic applications: An industrial perspective. Journal of Crystal Growth, 2008, 310, 4020-4026. | 0.7 | 113 |
| 8 | The progress of AlN bulk growth and epitaxy for electronic applications. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1153-1159. | 0.8 | 51 |
| 9 | Improve efficiency and long lifetime UVC LEDs with wavelengths between 230 and 237 nm. Applied Physics Express, 2020, 13, 022001. | 1.1 | 47 |
| 10 | On-wafer fabrication of etched-mirror UV-C laser diodes with the ALD-deposited DBR. Applied Physics Letters, 2020, 116, . | 1.5 | 42 |
| 11 | Design and characterization of a low-optical-loss UV-C laser diode. Japanese Journal of Applied Physics, 2020, 59, 094001. | 0.8 | 31 |
| 12 | AlGaIn Light-Emitting Diodes on AlN Substrates Emitting at 230 nm. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700660. | 0.8 | 29 |
| 13 | Space charge profile study of AlGaIn-based p-type distributed polarization doped claddings without impurity doping for UV-C laser diodes. Applied Physics Letters, 2020, 117, . | 1.5 | 26 |
| 14 | Molecular beam homoepitaxy on bulk AlN enabled by aluminum-assisted surface cleaning. Applied Physics Letters, 2020, 116, . | 1.5 | 26 |
| 15 | Surface control and MBE growth diagram for homoepitaxy on single-crystal AlN substrates. Applied Physics Letters, 2020, 116, . | 1.5 | 26 |
| 16 | Continuous-wave lasing of AlGaIn-based ultraviolet laser diode at 274.8 nm by current injection. Applied Physics Express, 2022, 15, 041007. | 1.1 | 25 |
| 17 | MBE growth and donor doping of coherent ultrawide bandgap AlGaIn alloy layers on single-crystal AlN substrates. Applied Physics Letters, 2021, 118, . | 1.5 | 16 |
| 18 | Impact of heat treatment process on threshold current density in AlGaIn-based deep-ultraviolet laser diodes on AlN substrate. Applied Physics Express, 2021, 14, 051003. | 1.1 | 9 |